



SISPAD 2019

Wednesday-Friday, 4-6 September

Palazzo di Toppo Wassermann
Università degli Studi di Udine
Udine, Italy



International Conference on Simulation of Semiconductor Processes and Devices (SISPAD) 2019

Conference Committee:

Conference Chair:

David Esseni, Univ. Udine

Technical Program Co-Chair:

Pierpaolo Palestri, Univ. Udine

Technical Program Co-Chair:

Denis Rideau, STMicroelectronics

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Daniel Connelly, Atomera

Sayed Hasan, Intel

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Sumeet Gupta, Purdue University

William Vandenberghe, Univ. Texas, Dallas

Seong-dong Kim, SK Hynix, South Korea

Kunikiyo Tatsuya, Renesas Electronics

Uihui Kwon, Samsung

Yiming Li, National Chiao Tung Univ., Taiwan

Satofumi Souma, Kobe University

Jeff Wu, TSMC, Taiwan

First Call for Papers

The 24th SISPAD conference will be held from September 4 to 6, 2019, in Udine, Italy.

Following the long term tradition of the SISPAD conference series as the leading forum for Technology Computer-Aided Design (TCAD), the conference provides an unique opportunity for the presentation and discussion of the latest advances in modeling and simulation of semiconductor devices, processes and equipment for integrated circuits and nanoelectronics.

The scientific program consists of invited and contributed presentations and a poster session. Companion tutorials are planned for September 3, 2019.

General Topics

- Modeling and simulation of all electron devices including FinFETs, GAA FETs, ultra-thin SOI devices, emerging memories devices, 2D materials devices, TFTs, sensors and biosensors, power electronic devices, tunnel FETs, ferroelectric FETs, spintronic devices, devices for neuromorphic and quantum computing, optoelectronic devices.
- Modeling and simulation of all sorts of semiconductor processes, including first-principles material design and growth simulation of nano-scale fabrication;
- Modeling and simulation of fabrication equipments
- Material level modeling
- Device level simulation
- Compact modeling for circuit simulation
- Modeling of device-circuit interactions
- Simulation of variability
- Interconnect modeling and algorithms
- Fundamental aspects and advanced numerical methods and algorithms
- Benchmarking, calibration and verification of simulators

Abstracts and Proceedings

Authors are invited to submit a two-page abstract (A4, 10 – 12 pt, pdf) excluding references, that can go on a third page. Submission information will be updated in the Second Call for Papers and at conference web site <http://www.sispad2019.org/>. Authors of accepted papers are requested to submit a four-page final paper which will be published in the conference proceedings and on IEEE Xplore Digital Library.

Important Dates

Abstract submission deadline: April 11, 2019

Notification of acceptance: June 10, 2019

Final paper: July 5, 2019

Further information and contacts

www.sispad2019.org

Organization Secretariat: Centro Congressi Internazionale.info@sispad2019.org

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